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Kind regards,

Team Nexperia

74HC3G04-Q100; 74HCT3G04-Q100

Inverter

Rev. 2 — 18 November 2013

Product data sheet

1. General description

The 74HC3G04-Q100; 74HCT3G04-Q100 is a triple inverter. Inputs include clamp diodes that enable the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade at 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$
- Input levels:
 - ◆ For 74HC3G04-Q100: CMOS level
 - ◆ For 74HCT3G04-Q100: TTL level
- Wide supply voltage range from 2.0 V to 6.0 V
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V ($C = 200\text{ pF}$, $R = 0\text{ }\Omega$)



3. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74HC3G04DP-Q100 74HCT3G04DP-Q100	-40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74HC3G04DC-Q100 74HCT3G04DC-Q100	-40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74HC3G04GD-Q100 74HCT3G04GD-Q100	-40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 3 × 2 × 0.5 mm	SOT996-2

4. Marking

Table 2. Marking codes

Type number	Marking code ^[1]
74HC3G04DP-Q100	H04
74HCT3G04DP-Q100	T04
74HC3G04DC-Q100	H04
74HCT3G04DC-Q100	T04
74HC3G04GD-Q100	H04
74HCT3G04GD-Q100	T04

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

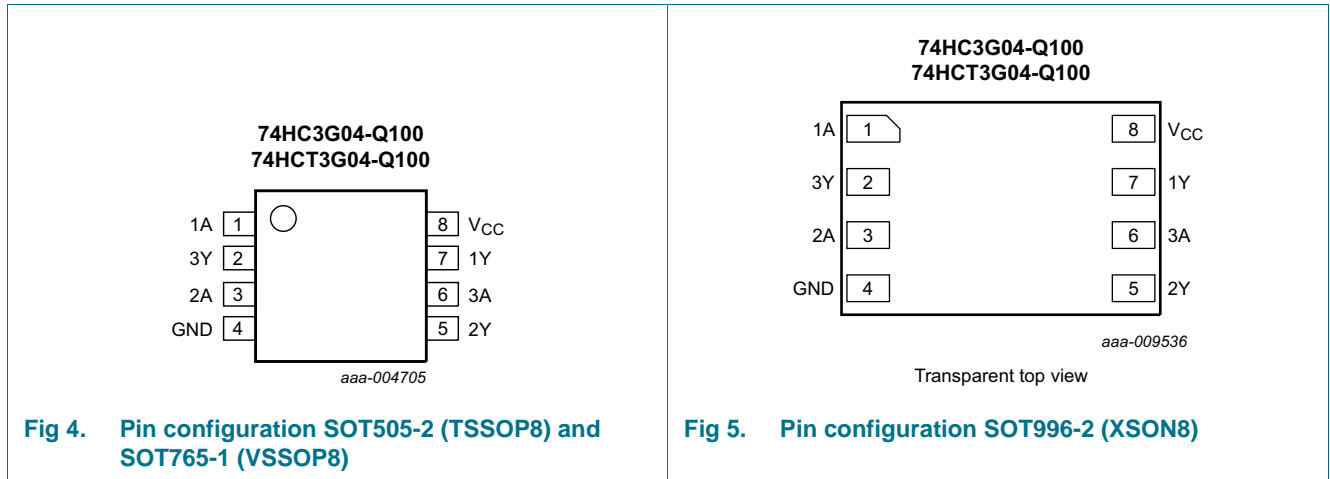
Fig 1. Logic symbol

Fig 2. IEC logic symbol

Fig 3. Logic diagram (one gate)

6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A, 2A, 3A	1, 3, 6	data input
GND	4	ground (0 V)
1Y, 2Y, 3Y	7, 5, 2	data output
V _{CC}	8	supply voltage

7. Functional description

Table 4. Function table^[1]

Input	Output
nA	nY
L	H
H	L

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	V _I < -0.5 V or V _I > V _{CC} + 0.5 V	[1] -	±20	mA
I _{OK}	output clamping current	V _O < -0.5 V or V _O > V _{CC} + 0.5 V	[1] -	±20	mA
I _O	output current	V _O = -0.5 V to (V _{CC} + 0.5 V)	[1] -	25	mA
I _{CC}	supply current		[1] -	50	mA
I _{GND}	ground current		[1] -50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _D	dynamic power dissipation	T _{amb} = -40 °C to +125 °C	[2] -	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.

For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.

For XSON8 package: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC3G04-Q100			74HCT3G04-Q100			Unit
			Min	Typ	Max	Min	Typ	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V _I	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
V _O	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V _{CC} = 6.0 V	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC3G04-Q100										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = -20 μA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = -20 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -20 μA; V _{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I _O = -4.0 mA; V _{CC} = 4.5 V	4.18	4.32	-	4.13	-	3.7	-	V
		I _O = -5.2 mA; V _{CC} = 6.0 V	5.68	5.81	-	5.63	-	5.2	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 20 μA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I _O = 5.2 mA; V _{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I _{CC}	supply current	per input pin; V _{CC} = 6.0 V; V _I = V _{CC} or GND; I _O = 0 A;	-	-	1.0	-	10	-	20	μA
C _I	input capacitance		-	1.5	-	-	-	-	-	pF

Table 7. Static characteristics ...continued

Voltages are referenced to GND (ground = 0 V). All typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HCT3G04-Q100										
V_{IH}	HIGH-level input voltage	$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	2.0	1.6	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	-	1.2	0.8	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}								
		$I_O = -20\text{ }\mu\text{A}$; $V_{CC} = 4.5\text{ V}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -4.0\text{ mA}$; $V_{CC} = 4.5\text{ V}$	4.18	4.32	-	4.13	-	3.7	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}								
		$I_O = 20\text{ }\mu\text{A}$; $V_{CC} = 4.5\text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0\text{ mA}$; $V_{CC} = 4.5\text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5\text{ V}$	-	-	± 0.1	-	± 1.0	-	± 1.0	μA
I_{CC}	supply current	per input pin; $V_{CC} = 5.5\text{ V}$; $V_I = V_{CC}$ or GND; $I_O = 0\text{ A}$;	-	-	1.0	-	10	-	20	μA
ΔI_{CC}	additional supply current	per input; $V_{CC} = 4.5\text{ V to }5.5\text{ V}$; $V_I = V_{CC} - 2.1\text{ V}$; $I_O = 0\text{ A}$	-	-	300	-	375	-	410	μA
C_I	input capacitance		-	1.5	-	-	-	-	-	pF

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); all typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$; for test circuit, see [Figure 7](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC3G04-Q100										
t_{pd}	propagation delay	nA to nY; see Figure 6 [1]								
		$V_{CC} = 2.0\text{ V}$	-	22	75	-	90	-	110	ns
		$V_{CC} = 4.5\text{ V}$	-	8	15	-	18	-	22	ns
		$V_{CC} = 6.0\text{ V}$	-	6	13	-	16	-	20	ns
t_t	transition time	see Figure 6 [2]								
		$V_{CC} = 2.0\text{ V}$	-	18	75	-	95	-	125	ns
		$V_{CC} = 4.5\text{ V}$	-	6	15	-	19	-	25	ns
		$V_{CC} = 6.0\text{ V}$	-	5	13	-	16	-	20	ns
C_{PD}	power dissipation capacitance	$V_I = \text{GND to } V_{CC}$ [3]	-	9	-	-	-	-	-	pF

Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); all typical values are measured at $T_{amb} = 25\text{ °C}$; for test circuit, see [Figure 7](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HCT3G04-Q100										
t_{pd}	propagation delay	nA to nY; see Figure 6 [1] $V_{CC} = 4.5\text{ V}$	-	10	18	-	23	-	29	ns
t_t	transition time	$V_{CC} = 4.5\text{ V}$; see Figure 6 [2]	-	6	15	-	19	-	22	ns
C_{PD}	power dissipation capacitance	$V_I = \text{GND to } V_{CC} - 1.5\text{ V}$ [3]	-	9	-	-	-	-	-	pF

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

[2] t_t is the same as t_{TLH} and t_{THL} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

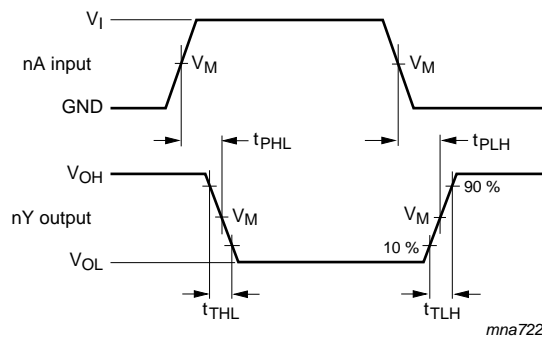
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

12. Waveforms



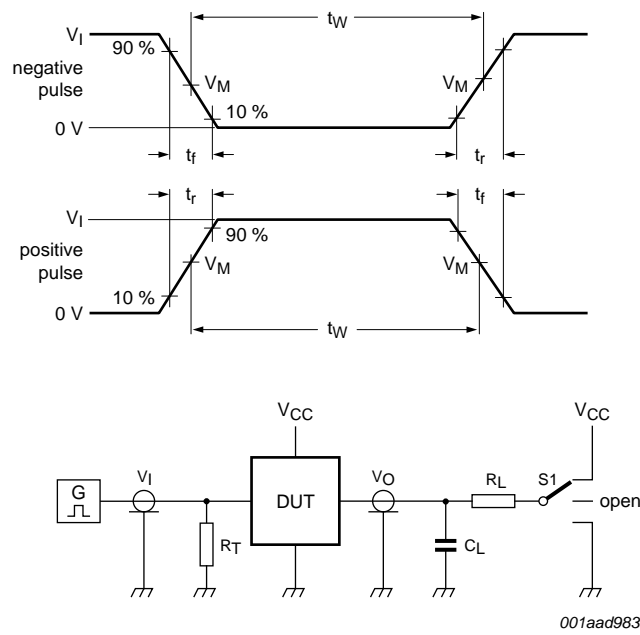
Measurement points are given in [Table 9](#).

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 6. The data input (nA) to output (nY) propagation delays

Table 9. Measurement points

Type	Input	Output
	V_M	V_M
74HC3G04-Q100	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74HCT3G04-Q100	1.3 V	1.3 V



Test data is given in [Table 10](#).

Definitions for test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch.

Fig 7. Test circuit for measuring switching times

Table 10. Test data

Type	Input		Load			S1 position
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	
74HC3G04-Q100	V_{CC}	≤ 6 ns	50 pF	1 k Ω	open	
74HCT3G04-Q100	3 V	≤ 6 ns	50 pF	1 k Ω	open	

13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

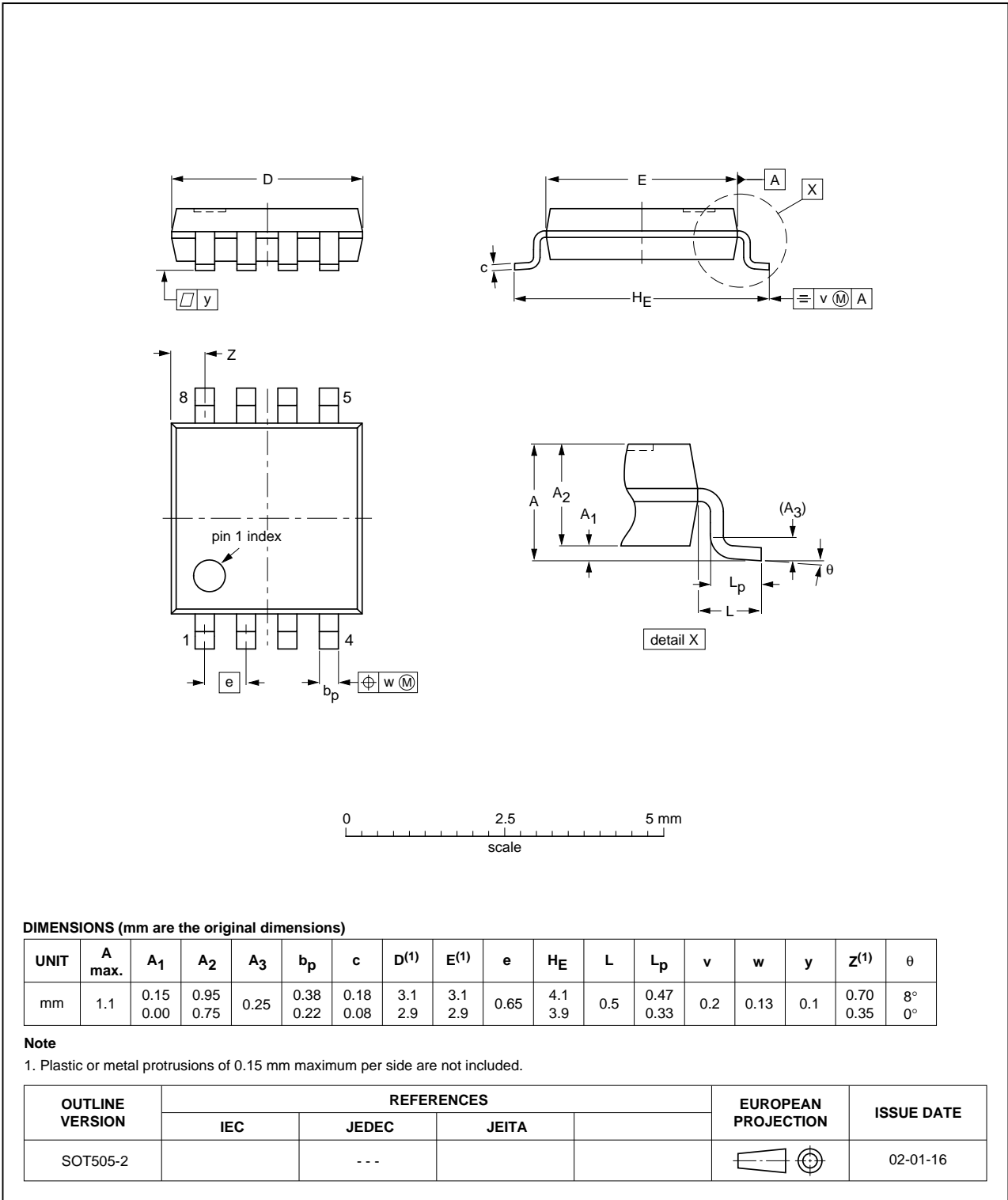


Fig 8. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

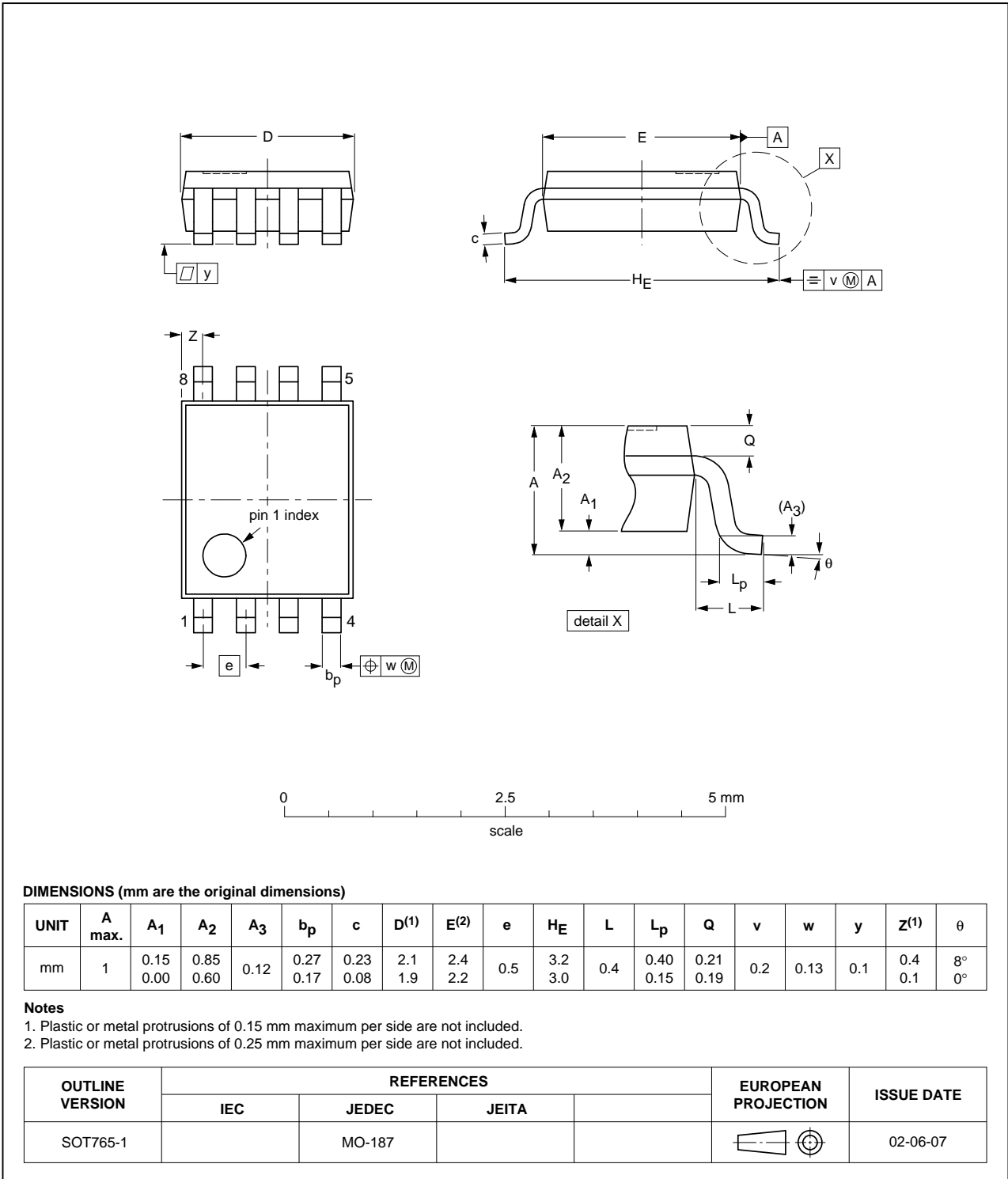


Fig 9. Package outline SOT765-1 (VSSOP8)

XSON8: plastic extremely thin small outline package; no leads;
8 terminals; body 3 x 2 x 0.5 mm

SOT996-2

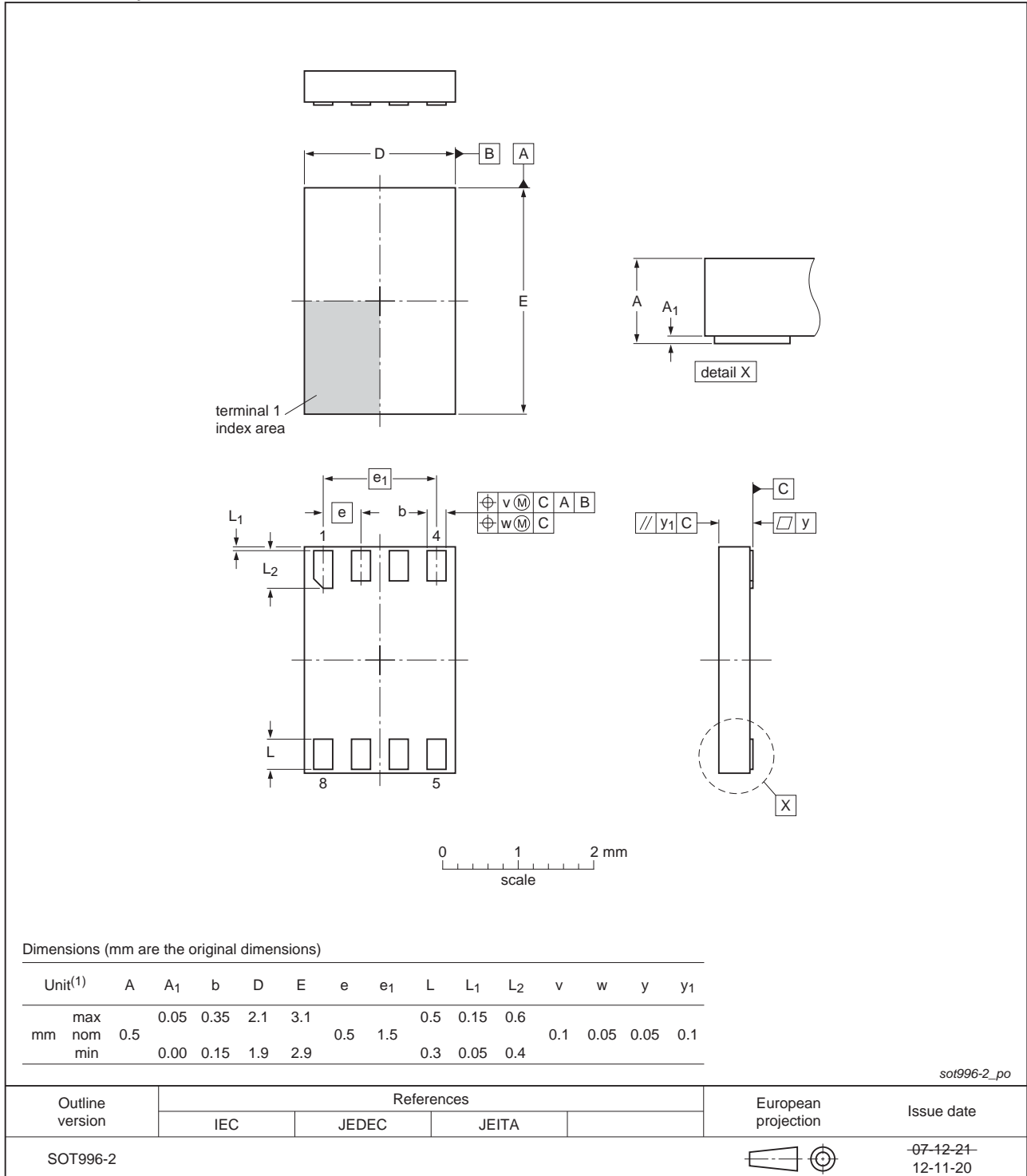


Fig 10. Package outline SOT996-2 (XSON8)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MIL	Military
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT3G04_Q100 v.2	20131118	Product data sheet	-	74HC_HCT3G04_Q100 v.1
Modifications:	<ul style="list-style-type: none">Added type numbers 74HC3G04GD-Q100 and 74HCT3G04GD-Q100 (XSON8 package)			
74HC_HCT3G04_Q100 v.1	20120827	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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